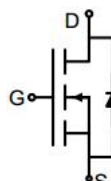
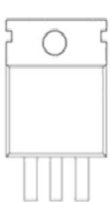



N-Channel Enhancement Mode Power MOSFET

| | | | |
|--|----------------|--|------------------|
| <p>Description</p> <p>The GT035N06T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● V_{DS} 60V ● I_D (at $V_{GS} = 10V$) 170A ● $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 3.5mΩ ● $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 4.5mΩ ● 100% Avalanche Tested ● RoHS Compliant <p>Application</p> <ul style="list-style-type: none"> ● Power switch ● DC/DC converters ● Synchronous Rectification | |  <p>Schematic Diagram</p>  <p>Marking and pin assignment</p>  <p>TO-220</p> | |
| Device | Package | Marking | Packaging |
| GT035N06T | TO-220 | GT035N06 | 50pcs/Tube |

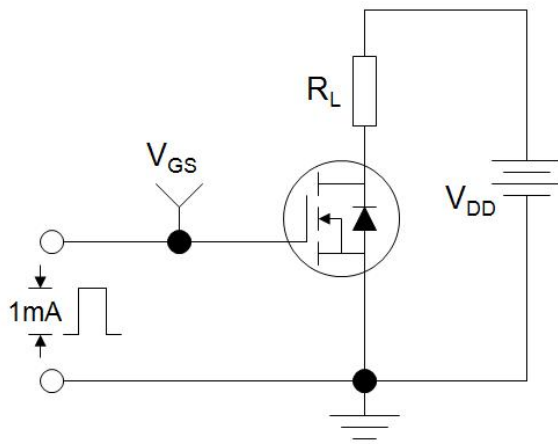
| Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted | | | |
|---|----------------|------------|--------------|
| Parameter | Symbol | Value | Unit |
| Drain-Source Voltage | V_{DS} | 60 | V |
| Continuous Drain Current | I_D | 170 | A |
| Pulsed Drain Current (note1) | I_{DM} | 300 | A |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Single pulse avalanche energy (note3) | E_{AS} | 256 | mJ |
| Power Dissipation | P_D | 215 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 To 150 | $^\circ C$ |
| Thermal Resistance | | | |
| Parameter | Symbol | Value | Unit |
| Thermal Resistance, Junction-to-Case | R_{thJA} | 50 | $^\circ C/W$ |
| Maximum Junction-to-Case | R_{thJC} | 0.58 | $^\circ C/W$ |

| Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|---------------|--|-------|------|-----------|------------|
| Parameter | Symbol | Test Conditions | Value | | | Unit |
| | | | Min. | Typ. | Max. | |
| Static Parameters | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$ | 60 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60V, V_{GS} = 0V$ | -- | -- | 1 | μA |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20V$ | -- | -- | ± 100 | nA |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1.2 | 1.6 | 2.5 | V |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 20A$ | -- | 2.5 | 3.5 | m Ω |
| | | $V_{GS} = 4.5V, I_D = 20A$ | -- | 3.0 | 4.5 | |
| Forward Transconductance | g_{FS} | $V_{DS} = 5V, I_D = 20A$ | -- | 60 | -- | S |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0\text{MHz}$ | -- | 5064 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 1100 | -- | |
| Reverse Transfer Capacitance | C_{rss} | | -- | 48 | -- | |
| Total Gate Charge | Q_g | $V_{DD} = 30V,$ $I_D = 20A,$ $V_{GS} = 10V$ | -- | 70 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 21 | -- | |
| Gate-Drain Charge | Q_{gd} | | -- | 16 | -- | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD} = 30V,$ $I_D = 50A,$ $R_G = 3\Omega$ | -- | 16 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 9 | -- | |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 36 | -- | |
| Turn-off Fall Time | t_f | | -- | 11 | -- | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Body Diode Current | I_S | $T_C = 25^\circ\text{C}$ | -- | -- | 125 | A |
| Body Diode Voltage | V_{SD} | $T_J = 25^\circ\text{C}, I_{SD} = 20A, V_{GS} = 0V$ | -- | -- | 1.2 | V |
| Reverse Recovery Charge | Q_{rr} | $I_F = 20A, di/dt = 500A/\mu s$ | | 150 | -- | nC |
| Reverse Recovery Time | T_{rr} | | | 30 | -- | ns |

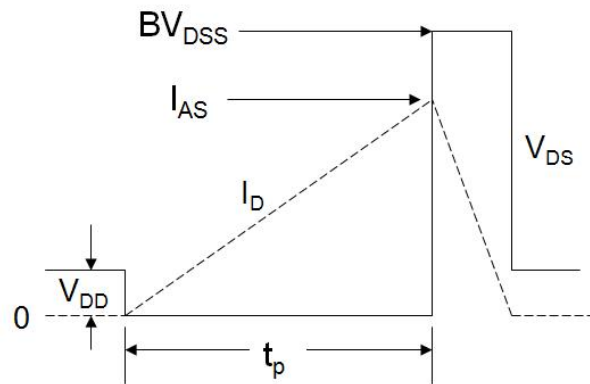
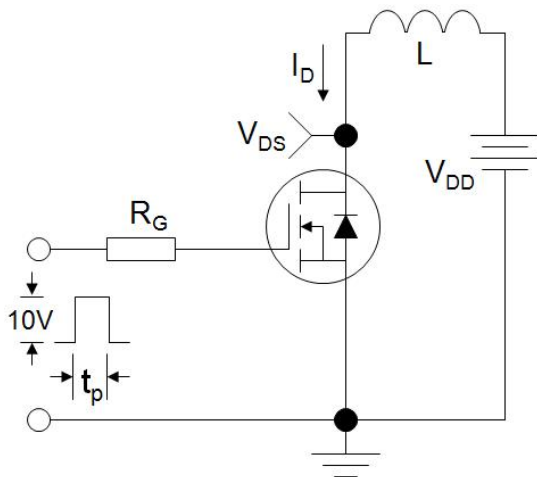
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 20A, V_{DD} = 40V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical R_G

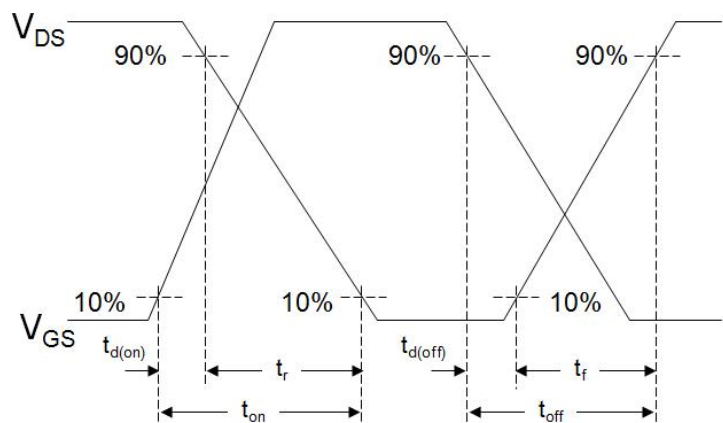
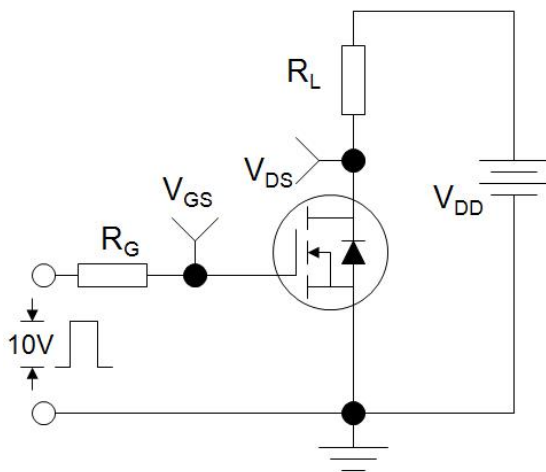
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

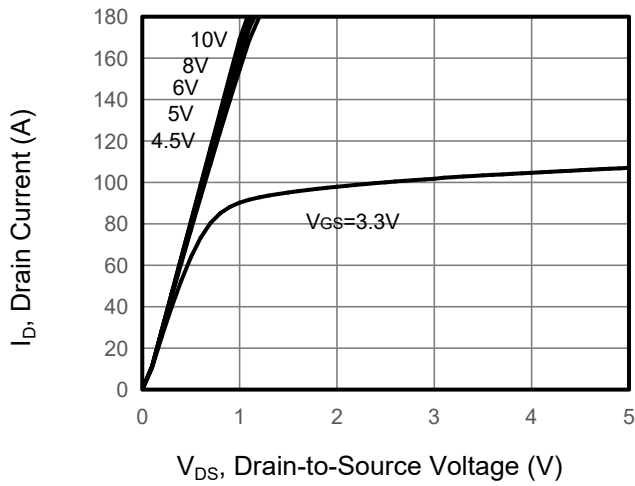


Figure 2. Transfer Characteristics

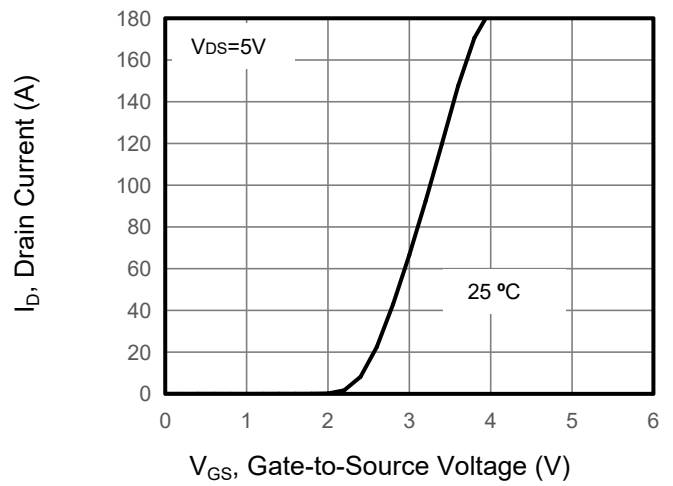


Figure 3. Gate Charge

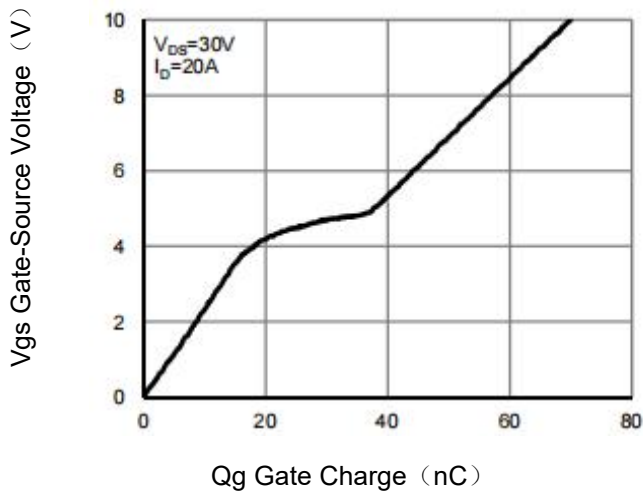


Figure 4. Drain Source On Resistance

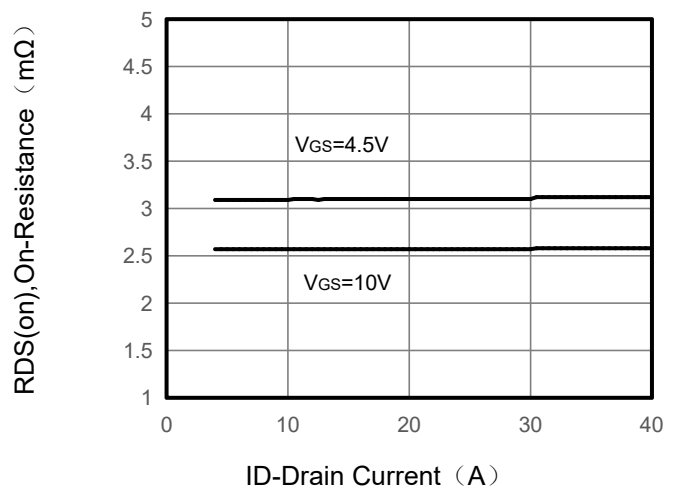


Figure 5. Capacitance vs Vds

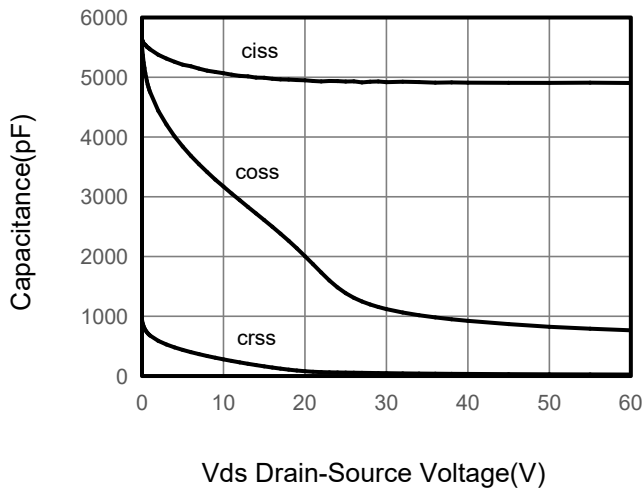
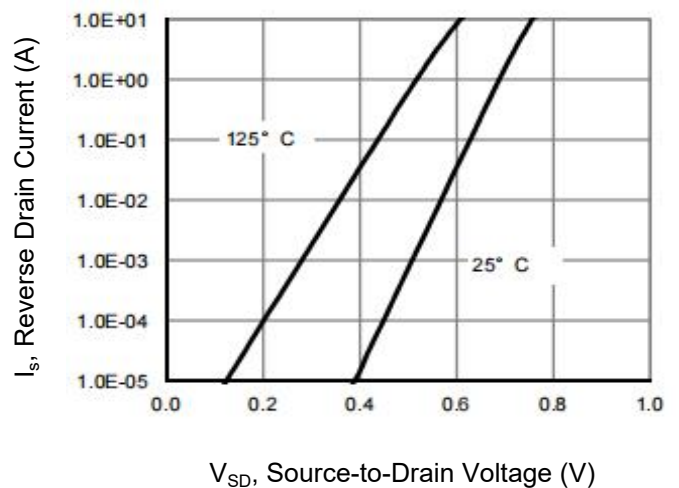


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

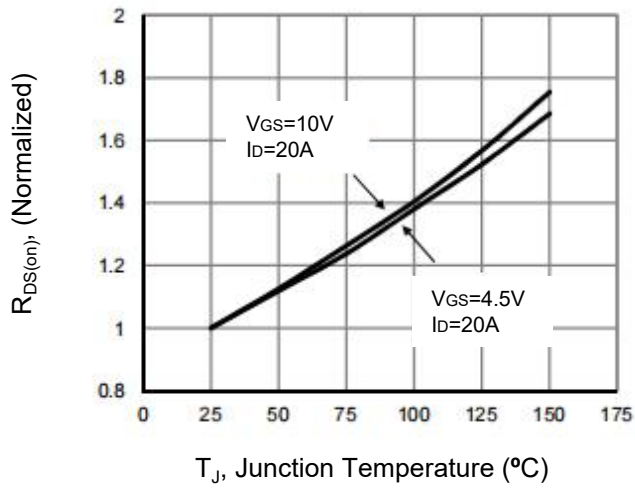


Figure 8. Safe Operation Area

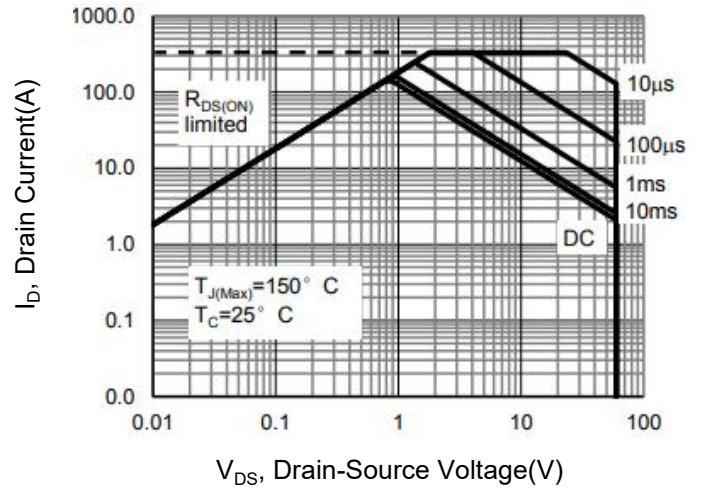
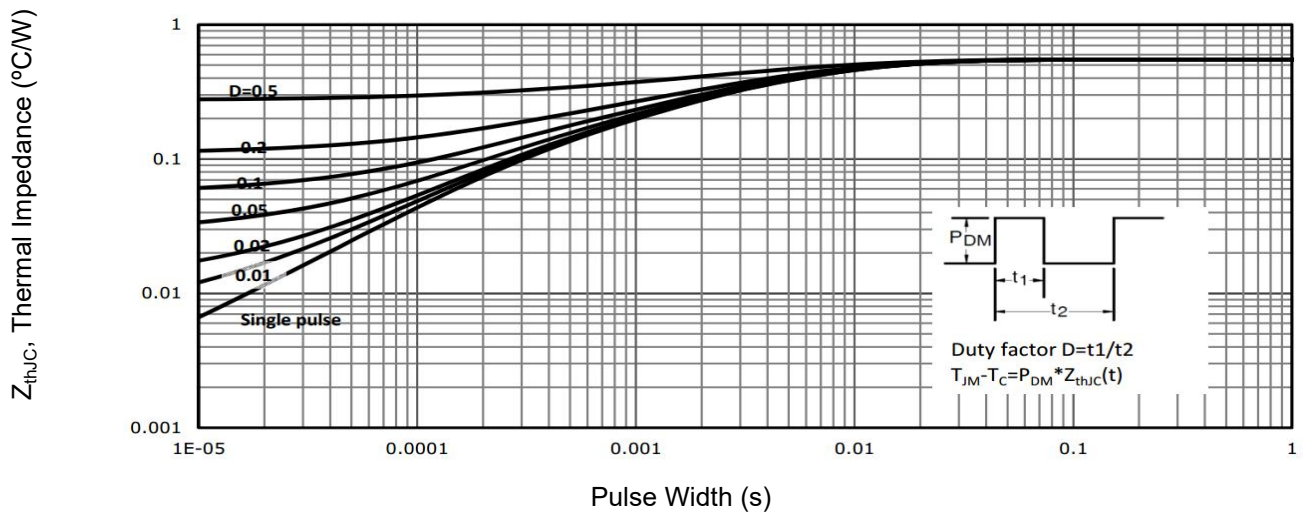
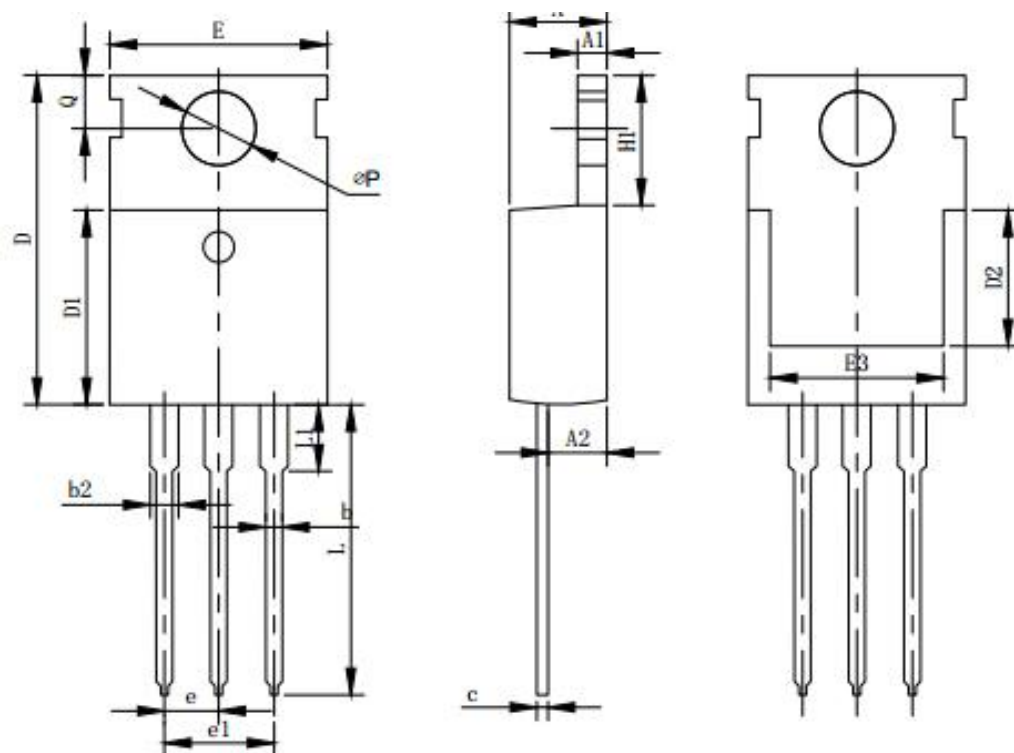


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



| Symbol | Dimensions in Millimeters | | |
|--------|---------------------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 4.37 | 4.57 | 4.7 |
| A1 | 1.25 | 1.3 | 1.4 |
| A2 | 2.2 | 2.4 | 2.6 |
| b | 0.7 | 0.8 | 0.95 |
| b2 | 1.7 | 1.27 | 1.47 |
| c | 0.45 | 0.5 | 0.6 |
| D | 15.1 | 15.6 | 16.1 |
| D1 | 8.8 | 9.1 | 9.4 |
| D2 | 5.5 | | |
| E | 9.7 | 10 | 10.3 |
| e | 2.54BSC | | |
| e1 | 5.08BSC | | |
| H1 | 6.25 | 6.5 | 6.85 |
| L | 12.75 | 13.5 | 13.8 |
| L1 | | 3.1 | 3.4 |
| ∅ P | 3.4 | 3.6 | 3.8 |
| Q | 2.6 | 2.8 | 3 |